



PRODUCT DATA SHEET



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Datasheet

Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

ESD Protection Diode

Features

- 350Watts peak pulse power (tp = 8/20µs)
- Unidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- IEC 61000-4-2 ±8kV contact ±15kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 10A (8/20µs)



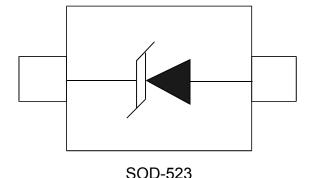
Applications

- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Pagers Peripherals

Mechanical Data

- SOD523 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Schematic & PIN Configuration





Absolute Maximum Rating

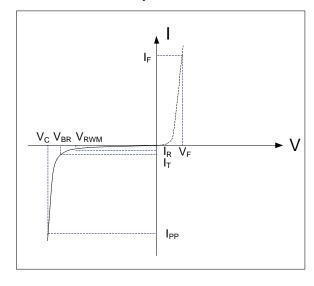
Albertate maximum rating					
Rating	Symbol	Value	Units		
Peak Pulse Power (t _p =8/20μs)	P _{PP}	350	Watts		
Peak Pulse Current (t _p =8/20µs) (note1)	I _{pp}	10	А		
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	15 8	kV		
Lead Soldering Temperature	TL	260(10seconds)	$^{\circ}$		
Junction Temperature	TJ	-55 to + 150	$^{\circ}$		
Storage Temperature	T _{stg}	-55 to + 150	$^{\circ}$		

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				12.0	V
Reverse Breakdown Voltage	V_{BR}	I _T =1mA	13.3			V
Reverse Leakage Current	I _R	V _{RWM} =12V,T=25℃			1	uA
Clamping Voltage	Vc	I _{PP} =10A,t _p =8/20μs			35	V
Junction Capacitance	C _j	V _R = 0V, f = 1MHz		55		pF

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter		
Ірр	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ IPP		
Vrwm	Working Peak Reverse Voltage		
Ir	Maximum Reverse Leakage Current @ Vrwм		
VBR	Breakdown Voltage @ IT		
IT	Test Current		



Note: $8/20\mu s$ pulsewaveform.



Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

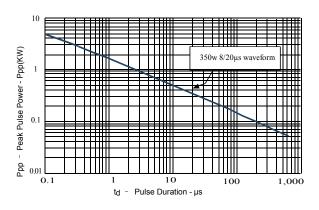


Figure 2: Power Derating Curve

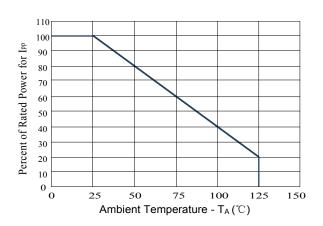


Figure3: Pulse Waveform

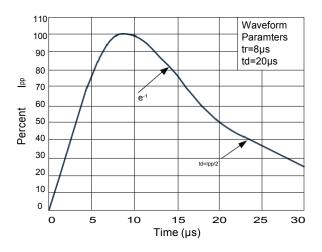
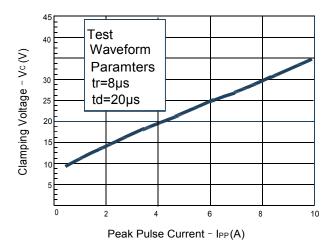
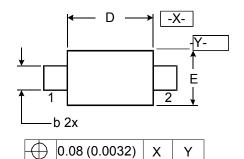


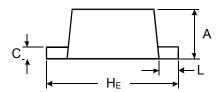
Figure 4: Clamping Voltage vs.lpp





Outline Drawing - SOD523





DIMENSIONS

SYMBOL	MILLIMETER		INCHES		
	MIN	MAX	MIN	MAX	
Α	0.50	0.70	0.020	0.028	
b	0.25	0.35	0.010	0.014	
С	0.07	0.20	0.0028	0.0079	
D	1.10	1.30	0.043	0.051	
E	0.70	0.90	0.028	0.035	
H _E	1.50	1.70	0.059	0.067	
L	0.15	0.25	0.006	0.010	



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